

TQHiP Process Cross-Section

Features

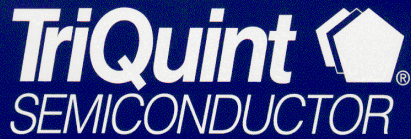
- Power MESFET Process
- Interconnects:
 - 2 Global (one airbridge)
 - 1 Local
- High-Q Passives
- Bulk & Thin Film Resistors
- Backside Vias Optional
- High Volume Production Processes
- Validated Models and Design Support

Applications

- Power Amplifiers
- Switches
- Frequencies thru X-Band
- Base Station Driver Amplifiers
- CATV Line Amplifiers
- Cellular Power Amps, Drivers, Switches

General Description

TriQuint's TQHiP process is our robust, high power density MESFET process. It provides a straight-forward, low cost process for a variety of circuits and applications. Its high operating and breakdown voltages make it ideal for wireless or wired infrastructure applications. A thick (4 μm) gold airbridge complements the 2 μm thick gold global metal and 0.5 μm thick gold surface layer for wiring flexibility and interconnect density. Precision NiCr resistors and high value MIM capacitors are included.



TQHiP

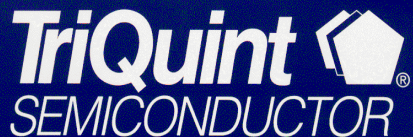
Power MESFET Foundry Service

**TQHiP
Process
Details**

TQHiP Process Details			
Element	Parameter	Value	Units
D-FET	Vp	-2.3	V
	Gate Length	0.5	um
	Idss	245	mA/mm
	I _{max}	370	mA/mm
	F _t @ 50% Idss	16.5	GHz
	F _{max}	60	GHz
	G _m	140	mS/mm
	BV _{gso} , Typical	9	V
	BV _{gdo} , Typical	14	V
	BV _{ds} , Typical	18	V
Interconnect	Metal Layers	3	
MIM Caps	Values	600	pF/mm ²
Resistors	NiCr	50	Ohms/sq
	Bulk	800	Ohms/sq
Inductors	Q	25	@ 2 GHz
Vias		Yes	
Mask Layers	No Vias	14	
	With Vias	16	

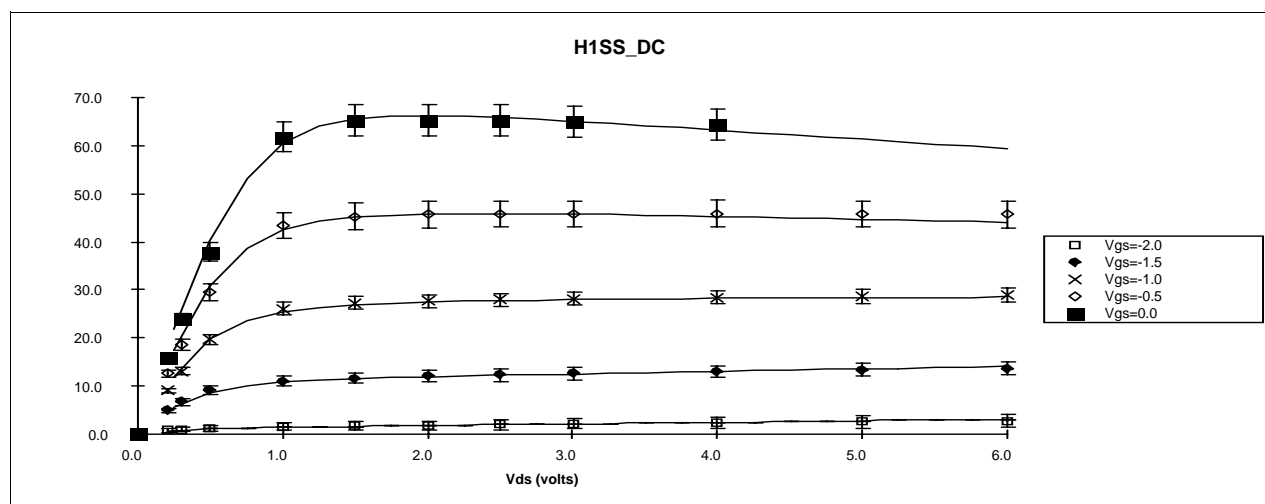
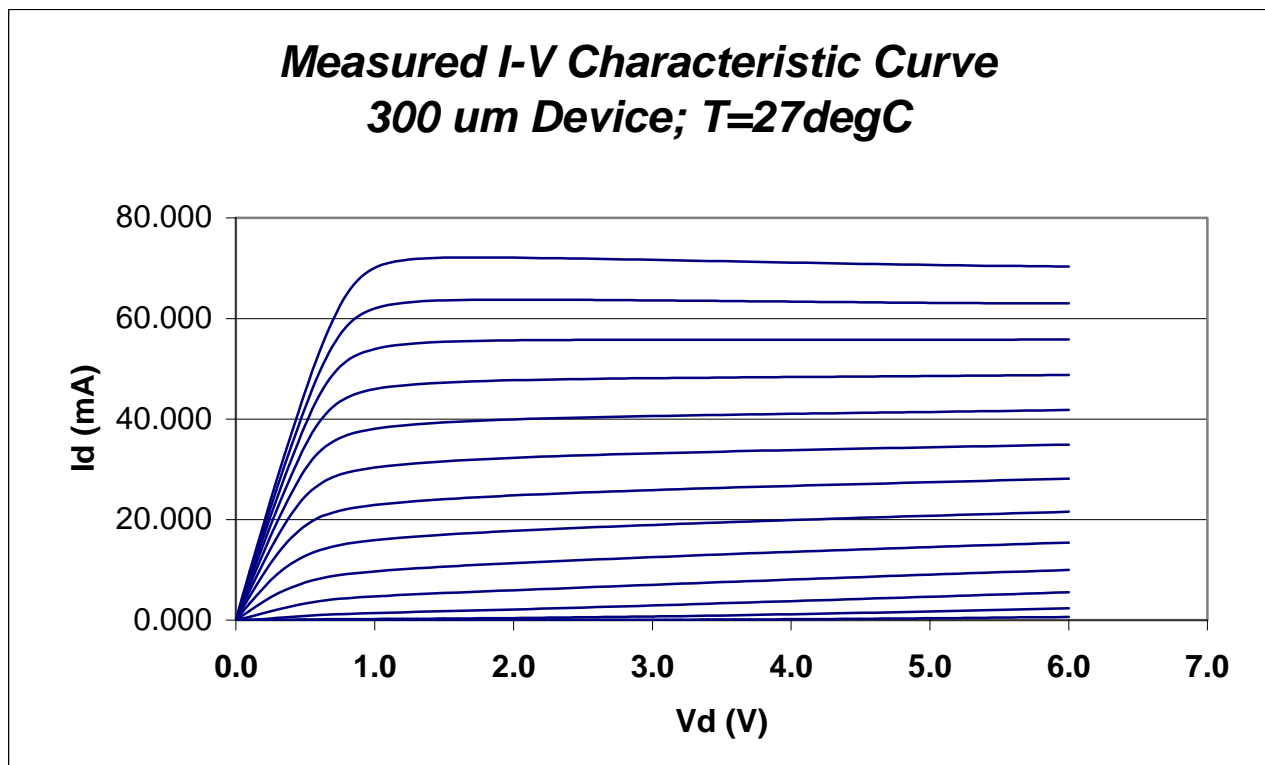
**Maximum
Ratings**

Operating Temperature Range	-65 to +150	°C
Capacitor Breakdown Voltage—Typ.	40	V
Min.	25	V

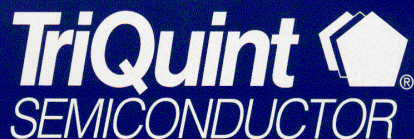


TQHiP

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Measured vs. Modeled DC Characteristics; H1SS - D1010 FET
($L_g = 1.0\text{mm}$, $L_{gs} = L_{gd} = 1.0\text{mm}$) Model Parameters; @ $T=27^\circ\text{C}$.



TQHiP

Power MESFET Foundry Service

Prototyping and Development

- Prototype Wafer Option (PWO):
 - Customer-specific Masks, Customer Schedule
 - 2 wafers delivered
 - Hot Lot Cycle Time
 - With thinning and sawing; optional backside vias
- Design Sensitivity Test Run (DST):
 - Yield Analysis
 - Design Sensitivity to Process Variation
 - 14 Wafer Start; Spread of Vp and Cgs values

Design Tools Available

- Device Library of Circuit Elements: FET, Diodes, Thin Film and Implanted Resistors, Capacitors, Inductors
- Parameters for "TriQuint's Own Model" (TOM) in Popular Simulators
- Agilent ADS Design Kit Available Now
- PSPICE Models Available Now
- Layout and Verification Kit for ICEditors Now
- Qualified Package Models for Supported Package Styles

Training

- GaAs Design Classes:
 - Half Day Introduction; Upon Request
 - Four Day Technical Training; Fall & Spring at TriQuint Oregon facility
- For Training and Schedules please visit:
www.triquint.com/foundry

Process Qualification Status

- TQHiP is a fully released and qualified process
- Reliability Reports
 - TQHiP Process Qualification
 - High Power Product Qualification
 - TQHiP Element Qualification Report
- For more information on Quality and Reliability, contact TriQuint or visit: www.triquint.com/manufacturing/QR/body_qr-pubs.htm

Applications Support Services

- Tiling of GDSII Stream Files including PCM
- Design Rule Check Services
- Layout versus Schematic Check Services
- Packaging Development Engineering
- Test Development Engineering:
 - On-Wafer
 - Packaged Parts
- Thermal Analysis Engineering
- Yield Enhancement Engineering
- Part Qualification Services
- Failure Analysis

Manufacturing Services

- Mask Making
- Production 150 Wafer Fab
- Wafer Thinning
- Wafer Sawing
- Substrate Vias
- DC Die Sort Testing
- RF On-Wafer Testing
- Plastic Packaging
- RF Packaged Part Testing

Please contact your local TriQuint Semiconductor Representative/ Distributor or Foundry Services Division Marketing for Additional information:
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